

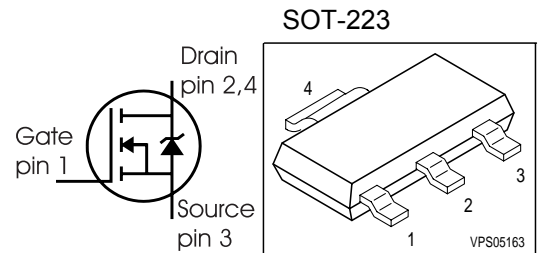
## SIPMOS<sup>®</sup> Small-Signal-Transistor

### Feature

- N-Channel
- Enhancement mode
- Logic Level
- dv/dt rated

### Product Summary

|              |      |          |
|--------------|------|----------|
| $V_{DS}$     | 200  | V        |
| $R_{DS(on)}$ | 1.8  | $\Omega$ |
| $I_D$        | 0.66 | A        |



| Type   | Package | Ordering Code | Tape and Reel Information | Marking |
|--------|---------|---------------|---------------------------|---------|
| BSP297 | SOT-223 | Q67000-S068   | E6327: 3000 pcs/reel      | BSP297  |

### Maximum Ratings, at $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

| Parameter   | Symbol              | Value                    | Unit              |
|---|---------------------|--------------------------|-------------------|
| Continuous drain current<br>$T_A=25\text{ }^\circ\text{C}$<br>$T_A=70\text{ }^\circ\text{C}$  | $I_D$               | 0.66<br>0.53             | A                 |
| Pulsed drain current<br>$T_A=25\text{ }^\circ\text{C}$  | $I_{D\text{ puls}}$ | 2.64                     |                   |
| Reverse diode dv/dt<br>$I_S=0.66\text{A}$ , $V_{DS}=160\text{V}$ , $di/dt=200\text{A}/\mu\text{s}$ , $T_{jmax}=150\text{ }^\circ\text{C}$ | dv/dt               | 6                        | kV/ $\mu\text{s}$ |
| Gate source voltage   | $V_{GS}$            | $\pm 20$                 | V                 |
| ESD Sensitivity (HBM) as per MIL-STD 883  |                     | Class 1                  |                   |
| Power dissipation<br>$T_A=25\text{ }^\circ\text{C}$   | $P_{tot}$           | 1.8                      | W                 |
| Operating and storage temperature<br>IEC climatic category; DIN IEC 68-1  | $T_j, T_{stg}$      | -55... +150<br>55/150/56 | $^\circ\text{C}$  |

**Thermal Characteristics**

| Parameter   | Symbol     | Values |          |           | Unit |
|---|------------|--------|----------|-----------|------|
|   |            | min.   | typ.     | max.      |      |
| <b>Characteristics</b>  |            |        |          |           |      |
| Thermal resistance, junction - soldering point<br>(Pin 4)   | $R_{thJS}$ | -      | 15       | 25        | K/W  |
| SMD version, device on PCB:<br>@ min. footprint<br>@ 6 cm <sup>2</sup> cooling area <sup>1)</sup> | $R_{thJA}$ | -<br>- | 80<br>48 | 115<br>70 |      |

**Electrical Characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

| Parameter  | Symbol        | Values |         |            | Unit          |
|--|---------------|--------|---------|------------|---------------|
|  |               | min.   | typ.    | max.       |               |
| <b>Static Characteristics</b>  |               |        |         |            |               |
| Drain-source breakdown voltage<br>$V_{GS}=0, I_D=250\mu\text{A}$   | $V_{(BR)DSS}$ | 200    | -       | -          | V             |
| Gate threshold voltage, $V_{GS} = V_{DS}$<br>$I_D=400\mu\text{A}$  | $V_{GS(th)}$  | 0.8    | 1.4     | 1.8        |               |
| Zero gate voltage drain current<br>$V_{DS}=200\text{V}, V_{GS}=0, T_j=25^\circ\text{C}$<br>$V_{DS}=200\text{V}, V_{GS}=0, T_j=150^\circ\text{C}$ | $I_{DSS}$     | -<br>- | -<br>10 | 0.1<br>100 | $\mu\text{A}$ |
| Gate-source leakage current<br>$V_{GS}=20\text{V}, V_{DS}=0$   | $I_{GSS}$     | -      | 1       | 10         |               |
| Drain-source on-state resistance<br>$V_{GS}=4.5\text{V}, I_D=0.53\text{A}$   | $R_{DS(on)}$  | -      | 1.2     | 3          | $\Omega$      |
| Drain-source on-state resistance<br>$V_{GS}=10\text{V}, I_D=0.66\text{A}$  | $R_{DS(on)}$  | -      | 1       | 1.8        |               |

<sup>1)</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic Characteristics**

|                              |              |   |      |      |      |    |
|------------------------------|--------------|---|------|------|------|----|
| Transconductance             | $g_{fs}$     | $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ ,<br>$I_D = 0.53\text{A}$ | 0.47 | 0.94 | -    | S  |
| Input capacitance            | $C_{iss}$    | $V_{GS} = 0$ , $V_{DS} = 25\text{V}$ ,                                  | -    | 286  | 357  | pF |
| Output capacitance           | $C_{oss}$    | $f = 1\text{MHz}$   | -    | 38   | 47   |    |
| Reverse transfer capacitance | $C_{rss}$    |   | -    | 15.7 | 23.5 |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD} = 100\text{V}$ , $V_{GS} = 4.5\text{V}$ ,                       | -    | 5.2  | 7.8  | ns |
| Rise time                    | $t_r$        | $I_D = 0.6\text{A}$ , $R_G = 15\Omega$                                  | -    | 3.8  | 5.7  |    |
| Turn-off delay time          | $t_{d(off)}$ |   | -    | 49   | 74   |    |
| Fall time                    | $t_f$        |   | -    | 19   | 29   |    |

**Gate Charge Characteristics**

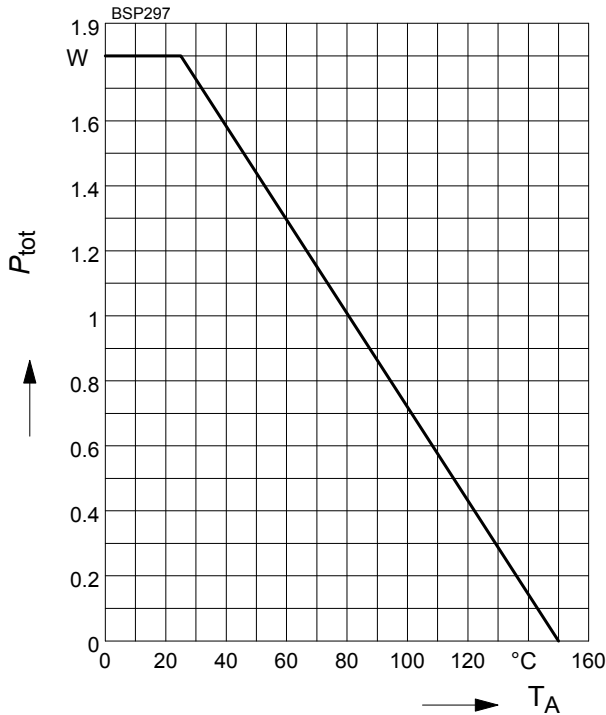
|                       |                 |   |   |      |      |    |
|-----------------------|-----------------|---|---|------|------|----|
| Gate to source charge | $Q_{gs}$        | $V_{DD} = 160\text{V}$ , $I_D = 0.66\text{A}$                                   | - | 0.7  | 0.9  | nC |
| Gate to drain charge  | $Q_{gd}$        |   | - | 5.2  | 7.8  |    |
| Gate charge total     | $Q_g$           | $V_{DD} = 160\text{V}$ , $I_D = 0.66\text{A}$ ,<br>$V_{GS} = 0$ to $10\text{V}$ | - | 12.9 | 16.1 |    |
| Gate plateau voltage  | $V_{(plateau)}$ | $V_{DD} = 160\text{V}$ , $I_D = 0.66\text{A}$                                   | - | 2.7  | 3.3  | V  |

**Reverse Diode**

|  |          |                                     |   |      |      |    |
|--|----------|-------------------------------------|---|------|------|----|
| Inverse diode continuous forward current | $I_S$    | $T_A = 25\text{ }^\circ\text{C}$    | - | -    | 0.66 | A  |
| Inv. diode direct current, pulsed        | $I_{SM}$ |                                     | - | -    | 2.64 |    |
| Inverse diode forward voltage            | $V_{SD}$ | $V_{GS} = 0$ , $I_F = I_S$          | - | 0.84 | 1.2  | V  |
| Reverse recovery time                    | $t_{rr}$ | $V_R = 100\text{V}$ , $I_F = I_S$ , | - | 52   | 78   | ns |
| Reverse recovery charge                  | $Q_{rr}$ | $di_F/dt = 100\text{A}/\mu\text{s}$ | - | 80   | 120  |    |

### 1 Power dissipation

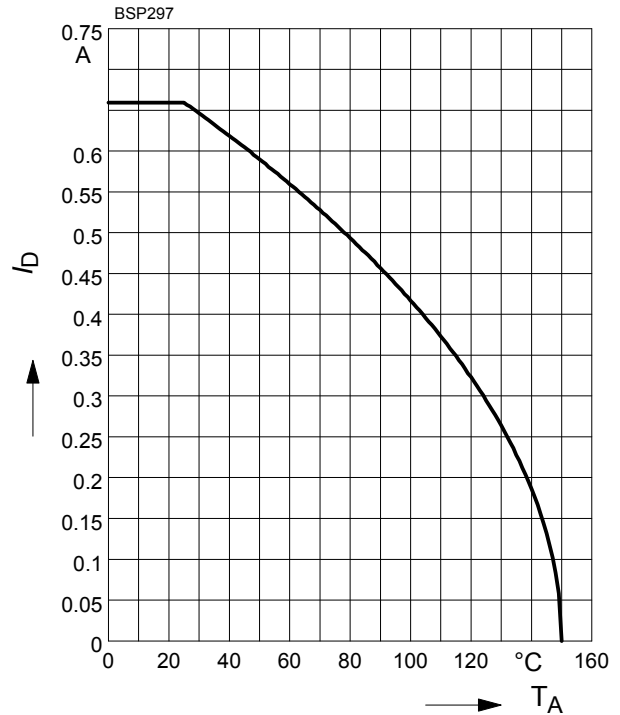
$$P_{tot} = f(T_A)$$



### 2 Drain current

$$I_D = f(T_A)$$

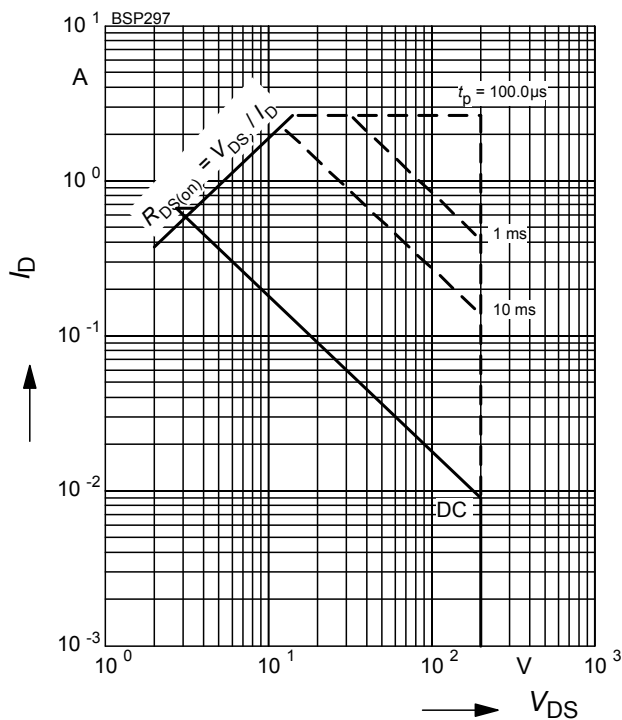
parameter:  $V_{GS} \geq 10\text{ V}$



### 3 Safe operating area

$$I_D = f(V_{DS})$$

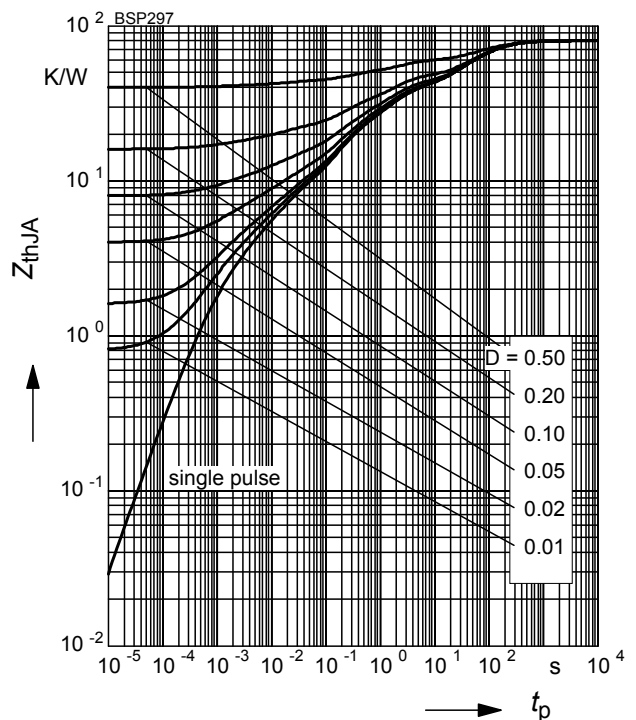
parameter:  $D = 0, T_A = 25\text{ °C}$



### 4 Transient thermal impedance

$$Z_{thJA} = f(t_p)$$

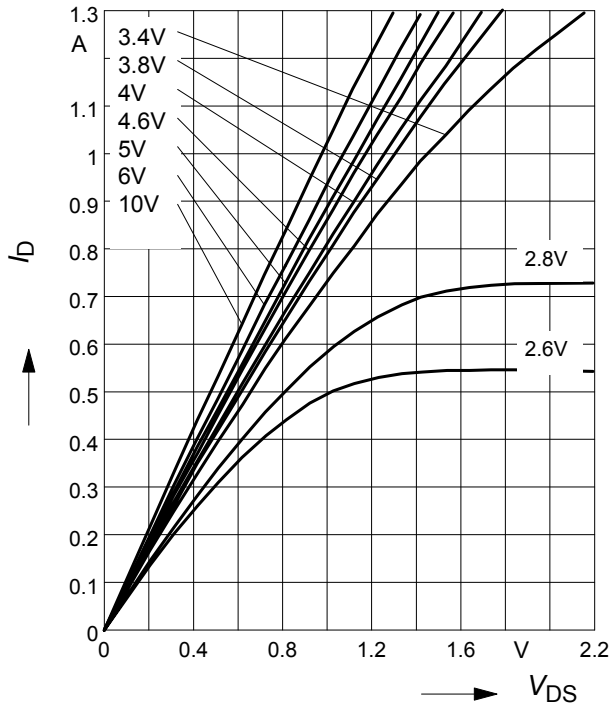
parameter:  $D = t_p/T$



**5 Typ. output characteristic**

$$I_D = f(V_{DS})$$

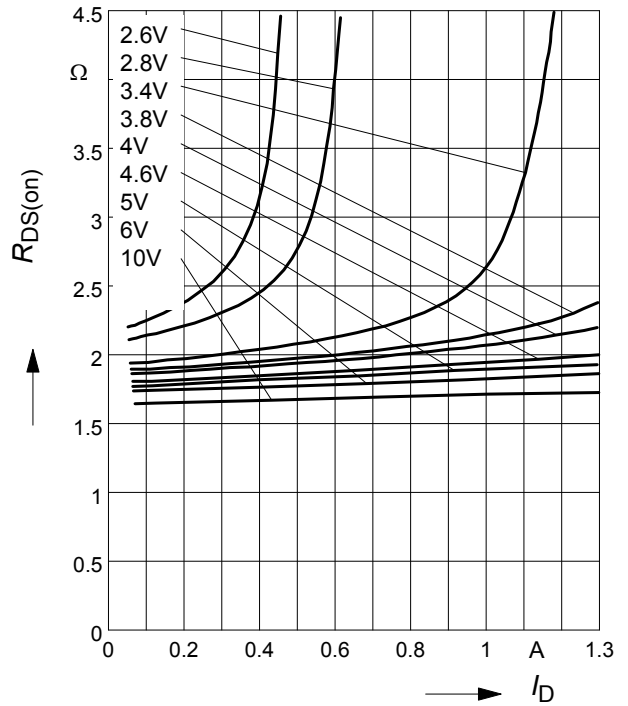
parameter:  $T_j = 25\text{ }^\circ\text{C}$ ,  $V_{GS}$



**6 Typ. drain-source on resistance**

$$R_{DS(on)} = f(I_D)$$

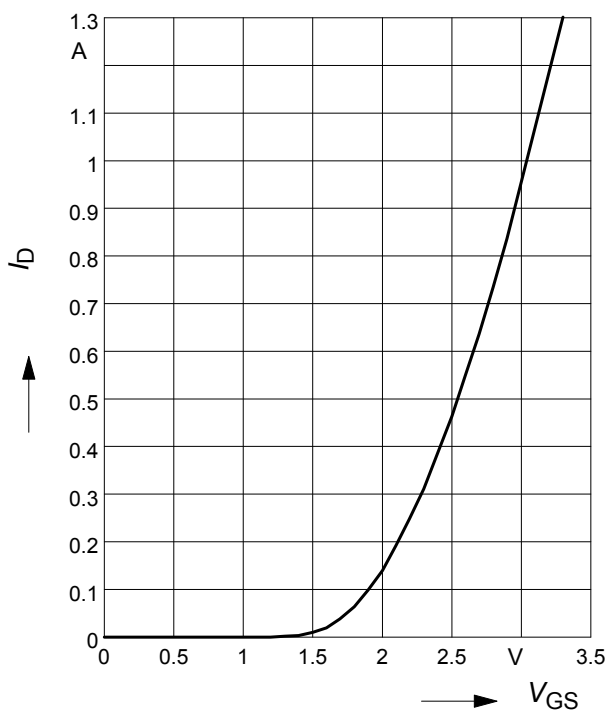
parameter:  $T_j = 25\text{ }^\circ\text{C}$ ,  $V_{GS}$



**7 Typ. transfer characteristics**

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

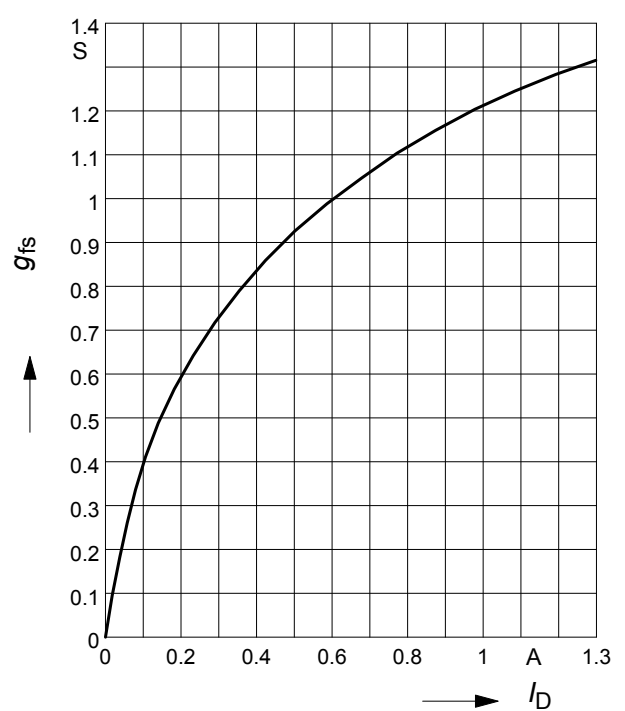
parameter:  $T_j = 25\text{ }^\circ\text{C}$



**8 Typ. forward transconductance**

$$g_{fs} = f(I_D)$$

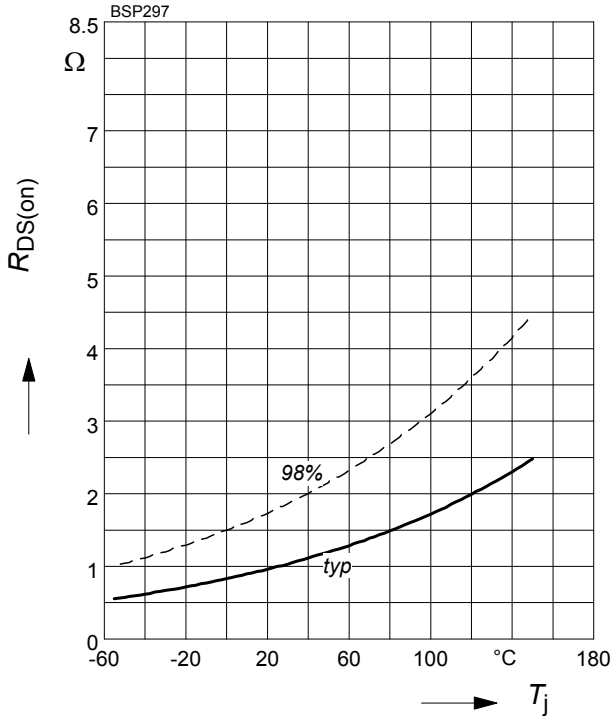
parameter:  $T_j = 25\text{ }^\circ\text{C}$



**9 Drain-source on-state resistance**

$$R_{DS(on)} = f(T_j)$$

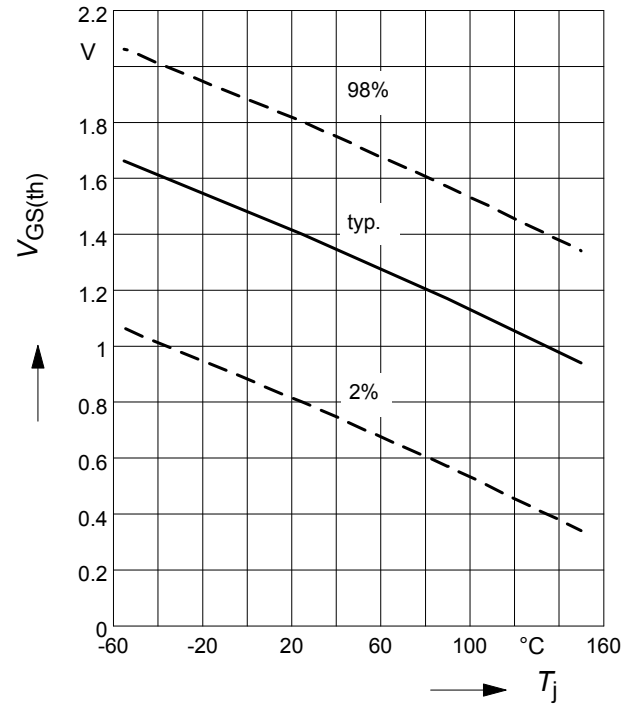
parameter:  $I_D = 0.66 \text{ A}$ ,  $V_{GS} = 10 \text{ V}$



**10 Typ. gate threshold voltage**

$$V_{GS(th)} = f(T_j)$$

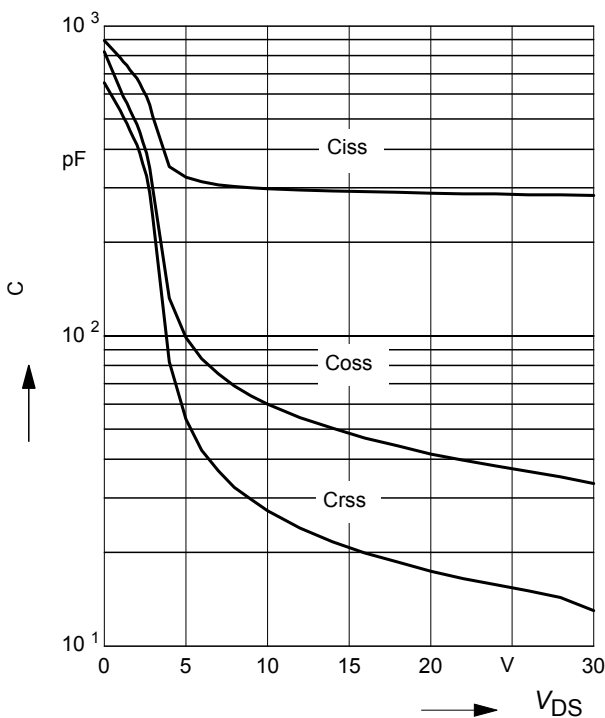
parameter:  $V_{GS} = V_{DS}$ ;  $I_D = 400 \mu\text{A}$



**11 Typ. capacitances**

$$C = f(V_{DS})$$

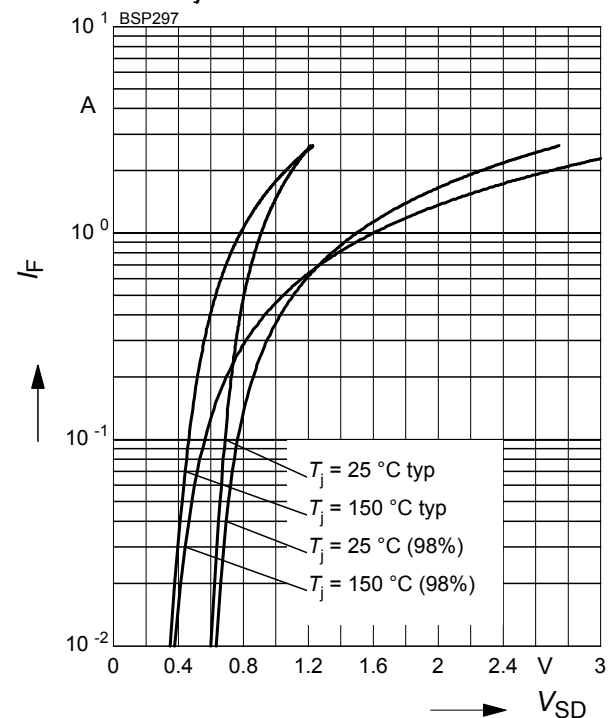
parameter:  $V_{GS} = 0$ ,  $f = 1 \text{ MHz}$ ,  $T_j = 25 \text{ }^\circ\text{C}$



**12 Forward character. of reverse diode**

$$I_F = f(V_{SD})$$

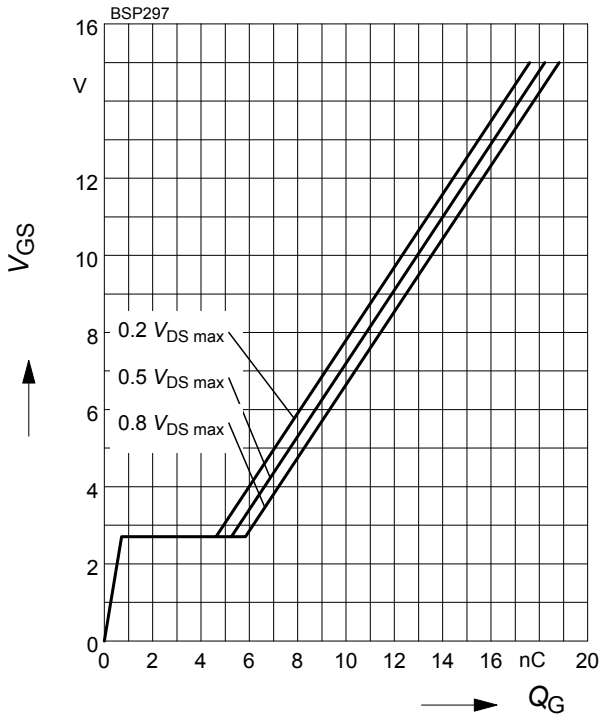
parameter:  $T_j$



**13 Typ. gate charge**

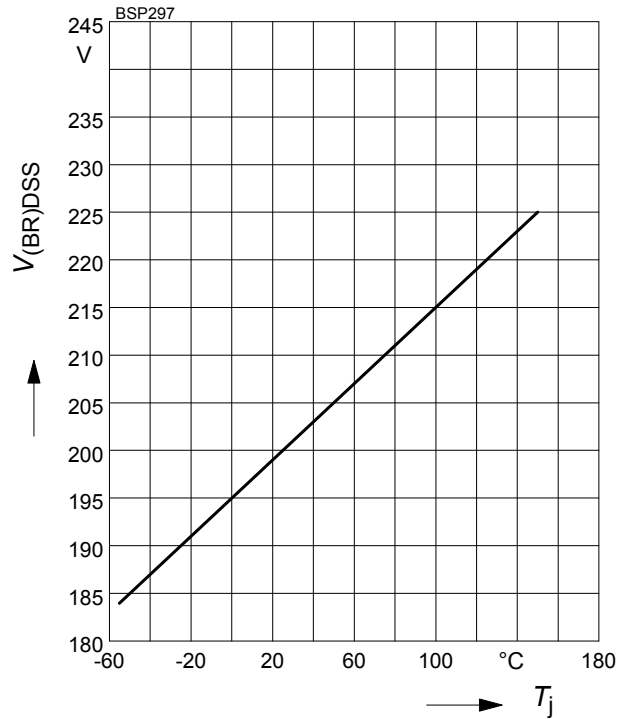
$V_{GS} = f(Q_G)$ ; parameter:  $V_{DS}$ ,

$I_D = 0.66$  A pulsed,  $T_j = 25$  °C



**14 Drain-source breakdown voltage**

$V_{(BR)DSS} = f(T_j)$



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